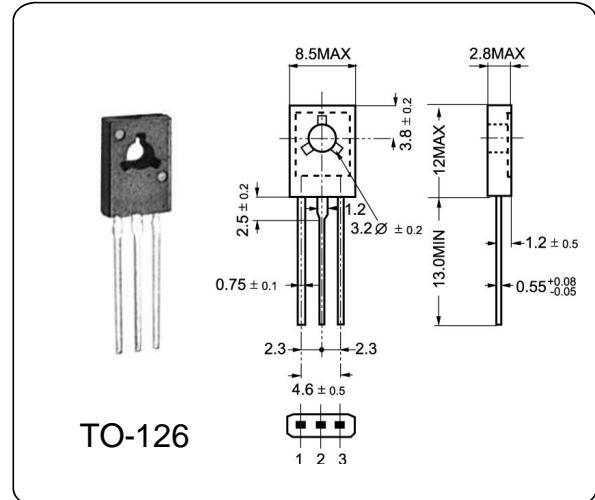


**DESCRIPTION**

It is intended for use in power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	3.0	A
Base Current	I _B	0.3	A
Total Dissipation at	P _{tot}	10	W
Max. Operating Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~150	°C

**ELECTRICAL CHARACTERISTICS (Ta = 25 °C)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I _{CEO}	V _{CB} =30V, I _E =0			0.01	mA
Emitter Cut-off Current	I _{EBO}	V _{EB} =3V, I _C =0			0.01	mA
Collector-Emitter Sustaining Voltage	V _{CEO}	I _C =10mA, I _B =0	30			V
DC Current Gain	h _{FE(1)}	V _{CE} =2V, I _C =20mA	30	150		
	h _{FE(2)}	V _{CE} =2V, I _C =1.0A	60	160	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =2A, I _B =200mA		0.3	0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =2A, I _B =200mA		1.0	2.0	V
Current Gain Bandwidth Product	f _T	V _{CE} =5V, I _C =100mA		90		MHz